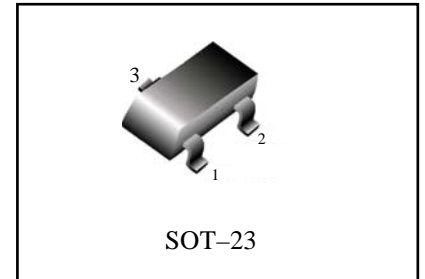


General Purpose Transistors

PNP Silicon

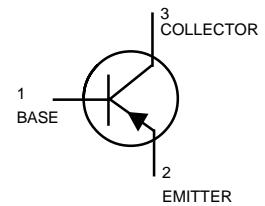
FEATURE

- Collector current capability $I_C = -800$ mA.
- Collector-emitter voltage $V_{CEO(max)} = -45$ V.
- General purpose switching and amplification.
- NPN complement : BC817 Series.



DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
BC807S-A	5A1	3000/Tape&Reel
BC807S-B	H5B	3000/Tape&Reel
BC807S-C	5C1	3000/Tape&Reel



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-45	V
Collector-Base Voltage	V_{CBO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-800	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = -10\text{ mA}$)	$V_{(BR)CEO}$	-45	—	—	V
Collector–Emitter Breakdown Voltage ($V_{EB} = 0, I_C = -10\ \mu\text{A}$)	$V_{(BR)CES}$	-50	—	—	V
Emitter–Base Breakdown Voltage ($I_E = -1.0\ \mu\text{A}$)	$V_{(BR)EBO}$	-5.0	—	—	V
Collector Cutoff Current ($V_{CB} = -20\text{ V}$) ($V_{CB} = -20\text{ V}, T_J = 150^\circ\text{C}$)	I_{CBO}	—	—	-100 -5.0	nA μA

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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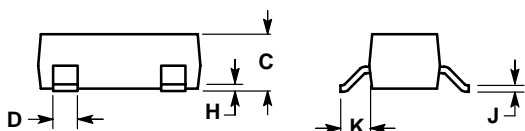
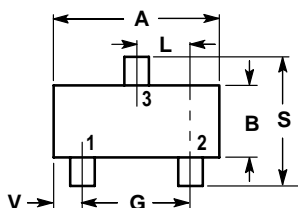
ON CHARACTERISTICS

DC Current Gain ($I_C = -100\text{ mA}, V_{CE} = -1.0\text{ V}$)	h_{FE}				—
	BC807–A	100	—	250	
	BC807–B	160	—	400	
	BC807–C	250	—	600	
($I_C = -500\text{ mA}, V_{CE} = -1.0\text{ V}$)		40	—	—	
Collector–Emitter Saturation Voltage ($I_C = -500\text{ mA}, I_B = -50\text{ mA}$)	$V_{CE(sat)}$	—	—	-0.7	V
Base–Emitter On Voltage ($I_C = -500\text{ mA}, I_B = -1.0\text{ V}$)	$V_{BE(on)}$	—	—	-1.2	V

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = -10\text{ mA}, V_{CE} = -5.0\text{ V}_{dc}, f = 100\text{ MHz}$)	f_T	100	—	—	MHz
Output Capacitance ($V_{CB} = -10\text{ V}, f = 1.0\text{ MHz}$)	C_{obo}	—	10	—	pF

SOT-23



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

